

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	110mΩ@-10V	-2.6A
	150mΩ@-4.5V	

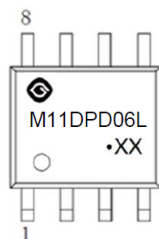
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge

Application

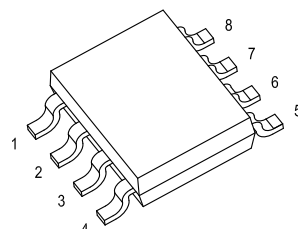
- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

MARKING:

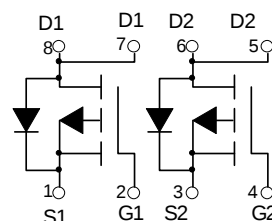


M11DPD06L = Device Code
 XX = Data Code
 Solid Dot = Green Device Indicator

SOP8



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ^{1,5}	$T_A = 25^\circ\text{C}$	I_D	-2.6	A
	$T_A = 100^\circ\text{C}$		-1.7	
Pulsed Drain Current ²		I_{DM}	-10	A
Power Dissipation ^{4,5}		P_D	1.34	W
$T_A = 25^\circ\text{C}$				
Single Pulsed Avalanche Current ⁶		I_{AS}	-9.5	A
Single Pulsed Avalanche Energy ⁶		E_{AS}	23	mJ
Thermal Resistance from Junction to Ambient ⁵		$R_{\theta JA}$	93	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~ +150	$^\circ\text{C}$

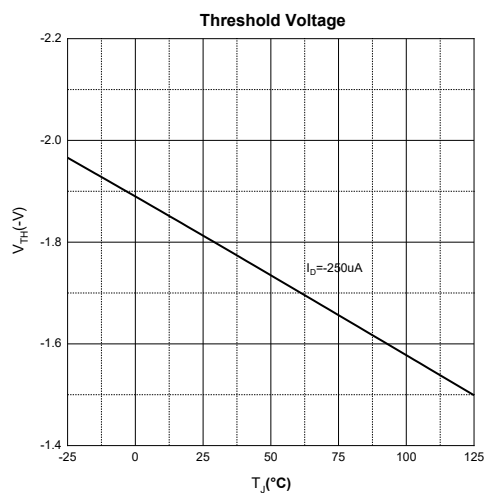
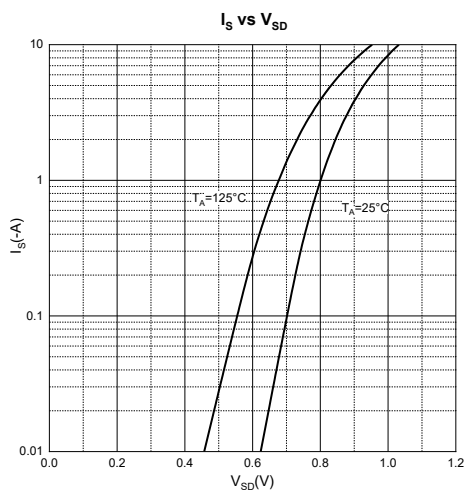
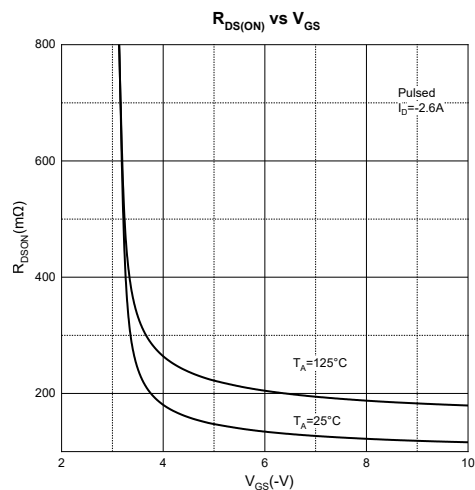
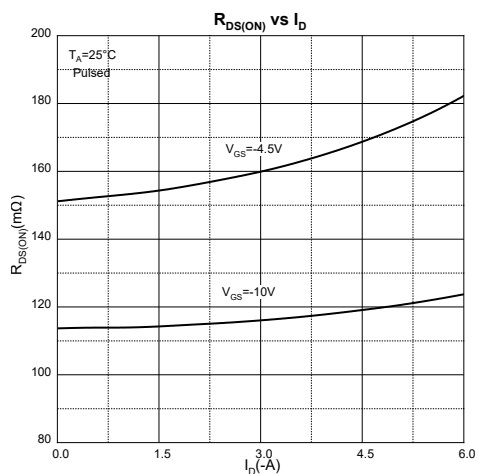
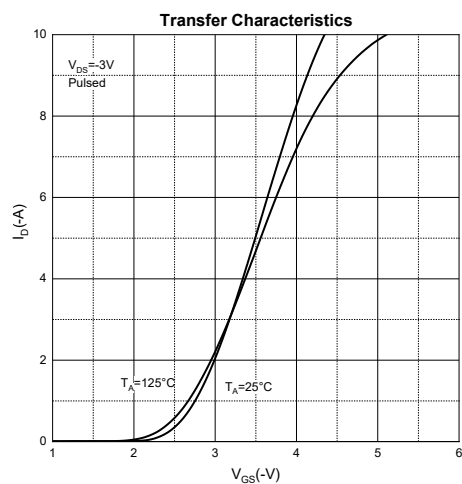
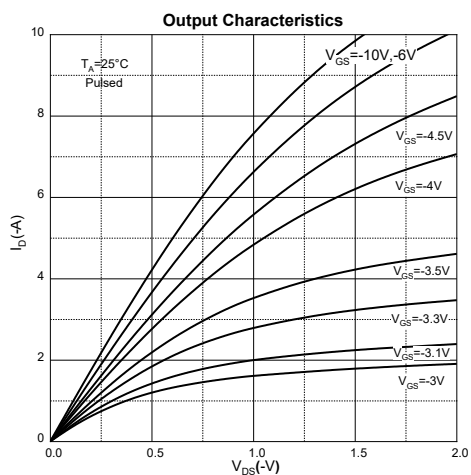
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

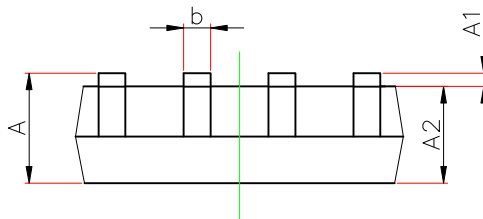
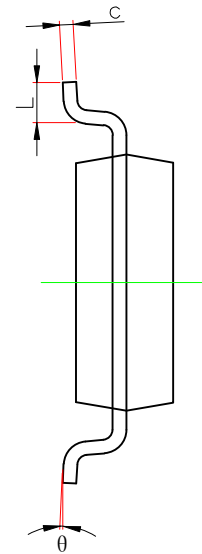
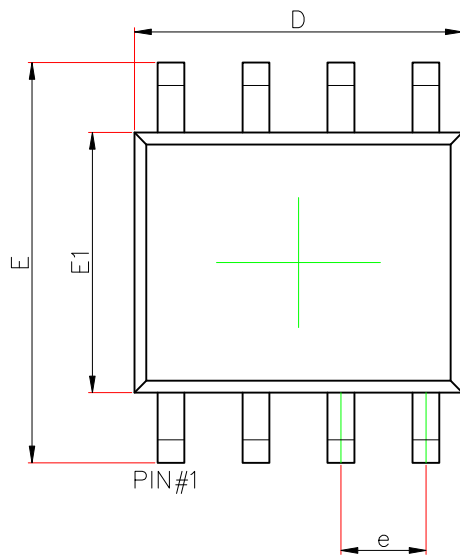
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics ³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	-1	-1.8	-3	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -2.6A$		110	160	m Ω
		$V_{GS} = -4.5V, I_D = -2.1A$		160	220	
Dynamic Characteristics ⁴						
Input Capacitance	C_{iss}	$V_{DS} = -30V, V_{GS} = 0V, f = 1MHz$		433		pF
Output Capacitance	C_{oss}			26		
Reverse Transfer Capacitance	C_{rss}			25		
Gate Resistance	R_g	$f = 1MHz$		4.8		Ω
Switching Characteristics ⁴						
Total Gate Charge	Q_g	$V_{DS} = -30V, V_{GS} = -10V, I_D = -2.6A$		10		nC
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			2.8		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30V, V_{GS} = -10V, R_L = 15\Omega, R_G = 3\Omega$		7		ns
Turn-On Rise Time	t_r			6		
Turn-Off Delay Time	$t_{d(off)}$			12		
Turn-Off Fall Time	t_f			7		
Source-Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -2A$			-1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.Pulse Test : Pulse Width ≤ 600μs, duty cycle ≤ 2%.
- 4.The power dissipation P_D is limited by T_{J(MAX)} = 150°C.
- 5.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.
- 6.EAS condition: V_{DD} = -60V, V_{GS} = -10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.

Typical Characteristics



SOP8 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.156	0.250	0.006	0.010
D	4.700	5.100	0.185	0.201
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
L	0.400	1.270	0.016	0.05
θ	0°	8°	0°	8°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.